

OVERVIEW

The CF5026 series are miniature crystal oscillator module ICs. They feature a damping resistor R_D matched to the crystal's characteristics to reduce crystal current. They support fundamental oscillation and 3rd overtone oscillation modes. The CF5026 series can be used to correspond to wide range of applications.

FEATURES

- Miniature-crystal matched oscillator characteristics
- Operating supply voltage range
 - 2.5V operation: 2.25 to 2.75V
 - 3.0V operation: 2.7 to 3.6V
- Recommended operating frequency range
 - For fundamental oscillator
 - CF5026ALx: 20MHz to 50MHz
 - CF5026BL1: 20MHz to 100MHz
 - For 3rd overtone oscillator
 - CF5026MLA: 70MHz to 80MHz
- -40 to 85°C operating temperature range
- Oscillator capacitor with excellent frequency characteristics built-in
- Oscillator circuit with damping resistor R_D built-in for reduced crystal current
- Standby function
 - High impedance in standby mode, oscillator stops
- Low standby current
 - Power-saving pull-up resistor built-in
- Oscillation detector function
- Frequency divider built-in (CF5026ALx)
 - Varies with version: f_O , $f_O/2$, $f_O/4$, $f_O/8$, $f_O/16$, $f_O/32$
- CMOS output duty level (1/2VDD)
- 50 ± 5% output duty @ 1/2VDD
- 30pF output load
- Molybdenum-gate CMOS process
- Chip form (CF5026xLx)

SERIES CONFIGURATION

Version	Operating supply voltage range [V]	Oscillation mode	Recommended operating frequency range (fundamental oscillation) ^{*1} [MHz]	Output current ($V_{DD} = 2.5V$) [mA]	Output frequency	Output duty level	Standby mode	
							Oscillator stop function	Output state
CF5026AL1	2.25 to 3.6	Fundamental	20 to 50	4	f_O	CMOS	Yes	Hi-Z
CF5026AL2					$f_O/2$			
CF5026AL3					$f_O/4$			
CF5026AL4					$f_O/8$			
CF5026AL5					$f_O/16$			
CF5026AL6					$f_O/32$			
CF5026BL1 ^{*2}	2.25 to 3.6	Fundamental	20 to 100	8	f_O	CMOS	Yes	Hi-Z
CF5026MLA	2.25 to 3.6	3rd overtone	70 to 80	8	f_O	CMOS	Yes	Hi-Z

*1. The recommended operating frequency is a yardstick value derived from the crystal used for NPC characteristics authentication. However, the oscillator frequency band is not guaranteed. Specifically, the characteristics can vary greatly due to crystal characteristics and mounting conditions, so the oscillation characteristics of components must be carefully evaluated.

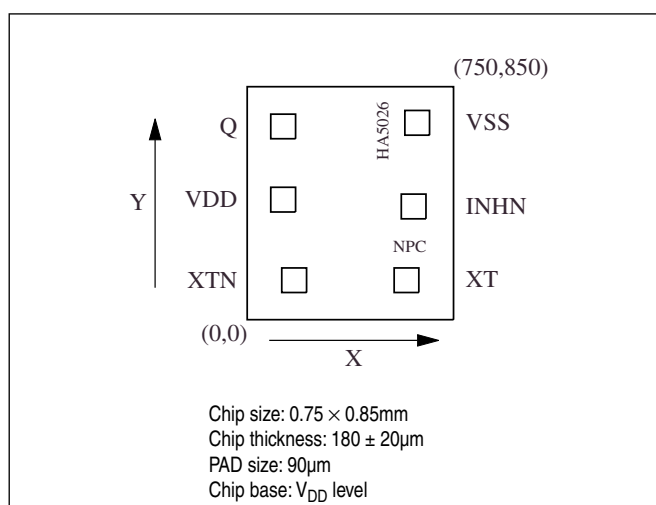
*2. The CF5026BL1 has a higher maximum operating frequency, hence the negative resistance is also larger than in the CF5026ALx devices.

ORDERING INFORMATION

Device	Package
CF5026xLx-3	Chip form

PAD LAYOUT

(Unit: μm)

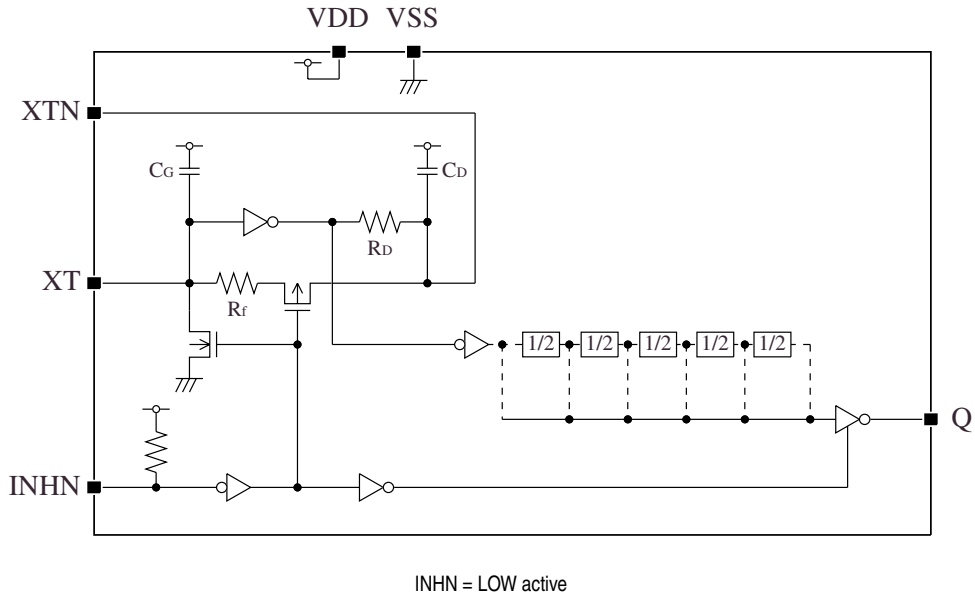


PIN DESCRIPTION and PAD DIMENSIONS

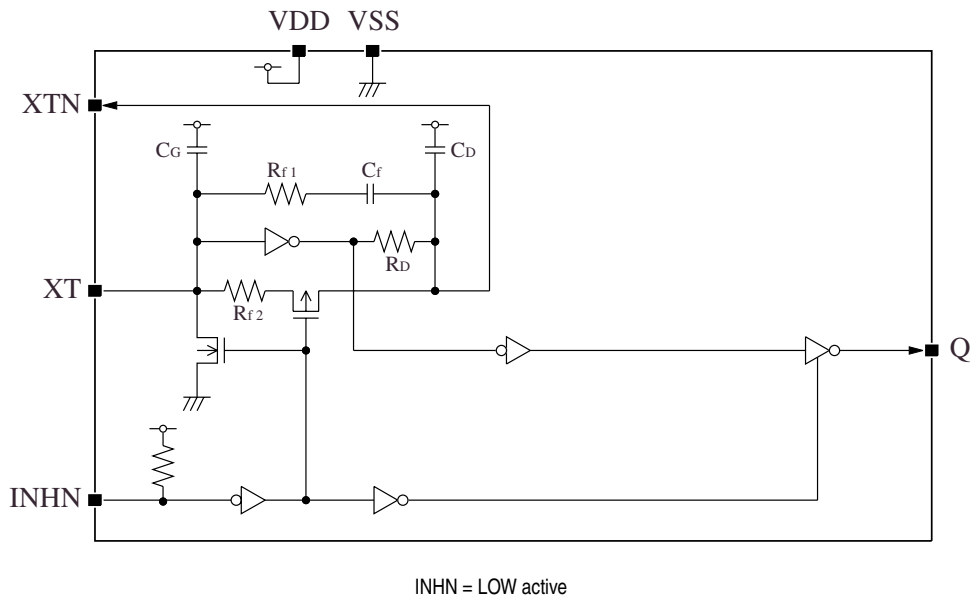
Name	I/O	Description	Pad dimensions [μm]	
			X	Y
INHN	I	Output state control input. High impedance when LOW (oscillator stops). Power-saving pull-up resistor built-in.	605	413
XT	I	Amplifier input	579	144
XTN	O	Amplifier output		
Crystal connection pins. Crystal is connected between XT and XTN.				
VDD	-	Supply voltage	131	438
Q	O	Output. Output frequency determined by internal circuit to one of f_0 , $f_0/2$, $f_0/4$, $f_0/8$, $f_0/16$, $f_0/32$. High impedance in standby mode	131	705
VSS	-	Ground	618	718

BLOCK DIAGRAM

For Fundamental Oscillator (CF5026AL×, CF5026BL1)



For 3rd Overtone Oscillator (CF5026MLA)



SPECIFICATIONS

Absolute Maximum Ratings

$V_{SS} = 0V$

Parameter	Symbol	Condition	Rating	Unit
Supply voltage range	V_{DD}		-0.5 to +7.0	V
Input voltage range	V_{IN}		-0.5 to $V_{DD} + 0.5$	V
Output voltage range	V_{OUT}		-0.5 to $V_{DD} + 0.5$	V
Operating temperature range	T_{opr}		-40 to +85	°C
Storage temperature range	T_{STG}		-65 to +150	°C
Output current	I_{OUT}		20	mA

Recommended Operating Conditions

$V_{SS} = 0V$, $C_L \leq 30pF$

Parameter	Symbol	Condition	Rating			Unit
			min	typ	max	
Operating supply voltage	V_{DD}		2.25	-	3.6	V
Input voltage	V_{IN}		V_{SS}	-	V_{DD}	V
Operating temperature	T_{OPR}		-40	-	+85	°C
Operating frequency	f_O	CF5026AL×	20	-	50	MHz
		CF5026BL1*1	20	-	100	MHz
		CF5026MLA	70	-	80	MHz

*1. When 2.5V operation, the ratings of switching characteristics are difference by the frequency or output load. Refer to CF5026BL1 switching characteristics (page 10).

Electrical Characteristics

CF5026AL× (2.5V operation)

$V_{DD} = 2.25$ to 2.75 V, $V_{SS} = 0$ V, $T_a = -40$ to $+85$ °C unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 2.25$ V, $I_{OH} = 4$ mA	1.65	1.95	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 2.25$ V, $I_{OL} = 4$ mA	–	0.3	0.4	V	
HIGH-level input voltage	V_{IH}	INH N	$0.7V_{DD}$	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	$0.3V_{DD}$	V	
Output leakage current	I_Z	Q: Measurement cct 2, INHN = LOW	$V_{OH} = V_{DD}$	–	–	10	μ A
			$V_{OL} = V_{SS}$	–	–	10	μ A
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INH N = open, $C_L = 30$ pF, $f = 50$ MHz	CF5026AL1	–	7	14	mA
			CF5026AL2	–	4.5	9	mA
			CF5026AL3	–	3.5	7	mA
			CF5026AL4	–	2.9	5.8	mA
			CF5026AL5	–	2.5	5.0	mA
			CF5026AL6	–	2.4	4.8	mA
Standby current	I_{ST}	Measurement cct 3, INHN = LOW	–	–	3	μ A	
INH N pull-up resistance	R_{UP1}	Measurement cct 4	2	6	12	M Ω	
	R_{UP2}		20	100	200	k Ω	
Feedback resistance	R_f	Measurement cct 5	50	–	150	k Ω	
Oscillator amplifier output resistance	R_D	Design value. A monitor pattern on a wafer is tested.	340	400	460	Ω	
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	6.8	8	9.2	pF	
	C_D		8.5	10	11.5	pF	

CF5026 series

CF5026AL× (3.0V operation)

$V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^{\circ}C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 2.7V$, $I_{OH} = 4mA$	2.3	2.4	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 2.7V$, $I_{OL} = 4mA$	–	0.3	0.4	V	
HIGH-level input voltage	V_{IH}	INH N	$0.7V_{DD}$	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	$0.3V_{DD}$	V	
Output leakage current	I_Z	Q: Measurement cct 2, INHN = LOW	$V_{OH} = V_{DD}$	–	–	10	μA
			$V_{OL} = V_{SS}$	–	–	10	μA
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INHN = open, $C_L = 30pF$, $f = 50MHz$	CF5026AL1	–	8.5	17	mA
			CF5026AL2	–	5.5	11	mA
			CF5026AL3	–	4	8	mA
			CF5026AL4	–	3.3	6.6	mA
			CF5026AL5	–	2.9	5.8	mA
			CF5026AL6	–	2.7	5.4	mA
Standby current	I_{ST}	Measurement cct 3, INHN = LOW	–	–	5	μA	
INH N pull-up resistance	R_{UP1}	Measurement cct 4	2	4	8	$M\Omega$	
	R_{UP2}		15	75	150	$k\Omega$	
Feedback resistance	R_f	Measurement cct 5	50	–	150	$k\Omega$	
Oscillator amplifier output resistance	R_D	Design value. A monitor pattern on a wafer is tested.	340	400	460	Ω	
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	6.8	8	9.2	pF	
	C_D		8.5	10	11.5	pF	

CF5026 series

CF5026BL1 (2.5V operation)

$V_{DD} = 2.25$ to $2.75V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^{\circ}C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 2.25V$, $I_{OH} = 8mA$	1.65	1.95	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 2.25V$, $I_{OL} = 8mA$	–	0.3	0.4	V	
HIGH-level input voltage	V_{IH}	INH N	$0.7V_{DD}$	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	$0.3V_{DD}$	V	
Output leakage current	I_Z	Q: Measurement cct 2, INH N = LOW	$V_{OH} = V_{DD}$	–	–	10	μA
			$V_{OL} = V_{SS}$	–	–	10	μA
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INH N = open, $C_L = 30pF$, $f = 100MHz$	–	14	28	mA	
Standby current	I_{ST}	Measurement cct 3, INH N = LOW	–	–	3	μA	
INH N pull-up resistance	R_{UP1}	Measurement cct 4	2	6	12	$M\Omega$	
	R_{UP2}		20	100	200	$k\Omega$	
Feedback resistance	R_f	Measurement cct 5	50	–	150	$k\Omega$	
Oscillator amplifier output resistance	R_D	Design value. A monitor pattern on a wafer is tested.	170	200	230	Ω	
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	6.8	8	9.2	pF	
	C_D		8.5	10	11.5	pF	

CF5026BL1 (3.0V operation)

$V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^{\circ}C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 2.7V$, $I_{OH} = 8mA$	2.3	2.4	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 2.7V$, $I_{OL} = 8mA$	–	0.3	0.4	V	
HIGH-level input voltage	V_{IH}	INH N	$0.7V_{DD}$	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	$0.3V_{DD}$	V	
Output leakage current	I_Z	Q: Measurement cct 2, INH N = LOW	$V_{OH} = V_{DD}$	–	–	10	μA
			$V_{OL} = V_{SS}$	–	–	10	μA
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INH N = open, $C_L = 30pF$, $f = 100MHz$	–	19	38	mA	
Standby current	I_{ST}	Measurement cct 3, INH N = LOW	–	–	5	μA	
INH N pull-up resistance	R_{UP1}	Measurement cct 4	2	4	8	$M\Omega$	
	R_{UP2}		15	75	150	$k\Omega$	
Feedback resistance	R_f	Measurement cct 5	50	–	150	$k\Omega$	
Oscillator amplifier output resistance	R_D	Design value. A monitor pattern on a wafer is tested.	170	200	230	Ω	
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	6.8	8	9.2	pF	
	C_D		8.5	10	11.5	pF	

CF5026 series

CF5026MLA (2.5V operation)

$V_{DD} = 2.25$ to $2.75V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^{\circ}C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 2.25V$, $I_{OH} = 8mA$	1.65	1.95	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 2.25V$, $I_{OL} = 8mA$	–	0.3	0.4	V	
HIGH-level input voltage	V_{IH}	INH N	$0.7V_{DD}$	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	$0.3V_{DD}$	V	
Output leakage current	I_Z	Q: Measurement cct 2, INHN = LOW	$V_{OH} = V_{DD}$	–	–	10	μA
			$V_{OL} = V_{SS}$	–	–	10	μA
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INHN = open, $C_L = 30pF$, $f = 72MHz$	–	11	22	mA	
Standby current	I_{ST}	Measurement cct 3, INHN = LOW	–	–	3	μA	
INH N pull-up resistance	R_{UP1}	Measurement cct 4	2	6	12	$M\Omega$	
	R_{UP2}		20	100	200	$k\Omega$	
AC feedback resistance	R_{f1}	Design value. A monitor pattern on a wafer is tested.	3.99	4.7	5.41	$k\Omega$	
DC feedback resistance	R_{f2}	Measurement cct 5	50	–	150	$k\Omega$	
Oscillator amplifier output resistance	R_D	Design value. A monitor pattern on a wafer is tested.	85	100	115	Ω	
AC feedback capacitance	C_f	Design value. A monitor pattern on a wafer is tested.	8.5	10	11.5	pF	
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	1.70	2	2.30	pF	
	C_D		3.40	4	4.60	pF	

CF5026MLA (3.0V operation)

$V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^{\circ}C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 2.7V$, $I_{OH} = 8mA$	2.3	2.4	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 2.7V$, $I_{OL} = 8mA$	–	0.3	0.4	V	
HIGH-level input voltage	V_{IH}	INH N	$0.7V_{DD}$	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	$0.3V_{DD}$	V	
Output leakage current	I_Z	Q: Measurement cct 2, INHN = LOW	$V_{OH} = V_{DD}$	–	–	10	μA
			$V_{OL} = V_{SS}$	–	–	10	μA
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INHN = open, $C_L = 30pF$, $f = 72MHz$	–	15	30	mA	
Standby current	I_{ST}	Measurement cct 3, INHN = LOW	–	–	5	μA	
INH N pull-up resistance	R_{UP1}	Measurement cct 4	2	4	8	$M\Omega$	
	R_{UP2}		15	75	150	$k\Omega$	
AC feedback resistance	R_{f1}	Design value. A monitor pattern on a wafer is tested.	3.99	4.7	5.41	$k\Omega$	
DC feedback resistance	R_{f2}	Measurement cct 5	50	–	150	$k\Omega$	
Oscillator amplifier output resistance	R_D	Design value. A monitor pattern on a wafer is tested.	85	100	115	Ω	
AC feedback capacitance	C_f	Design value. A monitor pattern on a wafer is tested.	8.5	10	11.5	pF	
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	1.70	2	2.30	pF	
	C_D		3.40	4	4.60	pF	

Switching Characteristics

CF5026AL× (2.5V operation)

$V_{DD} = 2.25$ to $2.75V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^{\circ}C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
Output rise time	t_{r1}	Measurement cct 3, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$	$C_L = 15pF$	–	3	6	ns
	t_{r2}		$C_L = 30pF$	–	5	10	ns
Output fall time	t_{f1}	Measurement cct 3, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$	$C_L = 15pF$	–	3	6	ns
	t_{f2}		$C_L = 30pF$	–	5	10	ns
Output duty cycle *1	Duty1	Measurement cct 3, load cct 1, $V_{DD} = 2.5V$, $T_a = 25^{\circ}C$, $f = 50MHz$	$C_L = 15pF$	45	–	55	%
	Duty2		$C_L = 30pF$	45	–	55	%
Output disable delay time *2	t_{PLZ}	Measurement cct 6, load cct 1, $V_{DD} = 2.5V$, $T_a = 25^{\circ}C$, $C_L = 15pF$		–	–	100	ns
Output enable delay time *2	t_{PZL}			–	–	100	ns

*1. The duty cycle characteristic is checked the sample chips of each production lot.

*2. Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

CF5026AL× (3.0V operation)

$V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^{\circ}C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
Output rise time	t_{r1}	Measurement cct 3, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$	$C_L = 15pF$	–	2.5	5	ns
	t_{r2}		$C_L = 30pF$	–	4.5	9	ns
Output fall time	t_{f1}	Measurement cct 3, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$	$C_L = 15pF$	–	2.5	5	ns
	t_{f2}		$C_L = 30pF$	–	4.5	9	ns
Output duty cycle *1	Duty1	Measurement cct 3, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^{\circ}C$, $f = 50MHz$	$C_L = 15pF$	45	–	55	%
	Duty2		$C_L = 30pF$	45	–	55	%
Output disable delay time *2	t_{PLZ}	Measurement cct 6, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^{\circ}C$, $C_L = 15pF$		–	–	100	ns
Output enable delay time *2	t_{PZL}			–	–	100	ns

*1. The duty cycle characteristic is checked the sample chips of each production lot.

*2. Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

CF5026 series

CF5026BL1 (2.5V operation)

$V_{DD} = 2.25$ to $2.75V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^{\circ}C$ unless otherwise noted.

Parameter	Symbol	Condition		Rating			Unit
				min	typ	max	
Output rise time	t_{r1}	Measurement cct 3, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$	$C_L = 15pF$	–	2	4	ns
	t_{r2}		$C_L = 30pF$	–	3	6	ns
	t_{r3}	Measurement cct 3, load cct 1, $0.2V_{DD}$ to $0.8V_{DD}$	$C_L = 30pF$	–	2.5	5	ns
Output fall time	t_{f1}	Measurement cct 3, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$	$C_L = 15pF$	–	2	4	ns
	t_{f2}		$C_L = 30pF$	–	3	6	ns
	t_{f3}	Measurement cct 3, load cct 1, $0.8V_{DD}$ to $0.2V_{DD}$	$C_L = 30pF$	–	2.5	5	ns
Output duty cycle ^{*1}	Duty1	Measurement cct 3, load cct 1, $V_{DD} = 2.5V$, $T_a = 25^{\circ}C$	$C_L = 15pF$ $f = 100MHz$	45	–	55	%
	Duty2		$C_L = 30pF$ $f = 80MHz$	45	–	55	%
	Duty3		$C_L = 30pF$ $f = 100MHz$	40	–	60	%
Output disable delay time ^{*2}	t_{PLZ}	Measurement cct 6, load cct 1, $V_{DD} = 2.5V$, $T_a = 25^{\circ}C$, $C_L = 15pF$		–	–	100	ns
Output enable delay time ^{*2}	t_{PZL}			–	–	100	ns

*1. The duty cycle characteristic is checked the sample chips of each production lot.

*2. Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

CF5026BL1 (3.0V operation)

$V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^{\circ}C$ unless otherwise noted.

Parameter	Symbol	Condition		Rating			Unit
				min	typ	max	
Output rise time	t_{r1}	Measurement cct 3, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$	$C_L = 15pF$	–	1.5	3	ns
	t_{r2}		$C_L = 30pF$	–	2.5	5	ns
Output fall time	t_{f1}	Measurement cct 3, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$	$C_L = 15pF$	–	1.5	3	ns
	t_{f2}		$C_L = 30pF$	–	2.5	5	ns
Output duty cycle ^{*1}	Duty1	Measurement cct 3, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^{\circ}C$, $f = 100MHz$	$C_L = 15pF$	45	–	55	%
	Duty2		$C_L = 30pF$	45	–	55	%
Output disable delay time ^{*2}	t_{PLZ}	Measurement cct 6, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^{\circ}C$, $C_L = 15pF$		–	–	100	ns
Output enable delay time ^{*2}	t_{PZL}			–	–	100	ns

*1. The duty cycle characteristic is checked the sample chips of each production lot.

*2. Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

CF5026MLA (2.5V operation)

$V_{DD} = 2.25$ to $2.75V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^{\circ}C$ unless otherwise noted.

Parameter	Symbol	Condition		Rating			Unit
				min	typ	max	
Output rise time	t_{r1}	Measurement cct 3, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$	$C_L = 15pF$	–	2	4	ns
	t_{r2}		$C_L = 30pF$	–	3	6	ns
Output fall time	t_{f1}	Measurement cct 3, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$	$C_L = 15pF$	–	2	4	ns
	t_{f2}		$C_L = 30pF$	–	3	6	ns
Output duty cycle ^{*1}	Duty1	Measurement cct 3, load cct 1, $V_{DD} = 2.5V$, $T_a = 25^{\circ}C$, $f = 72MHz$	$C_L = 15pF$	45	–	55	%
	Duty2		$C_L = 30pF$	45	–	55	%
Output disable delay time ^{*2}	t_{PLZ}	Measurement cct 6, load cct 1, $V_{DD} = 2.5V$, $T_a = 25^{\circ}C$, $C_L = 15pF$		–	–	100	ns
Output enable delay time ^{*2}	t_{PZL}			–	–	100	ns

*1. The duty cycle characteristic is checked the sample chips of each production lot.

*2. Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

CF5026MLA (3.0V operation)

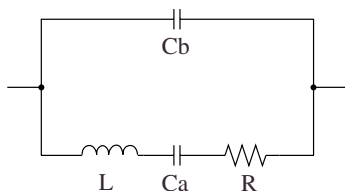
$V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^{\circ}C$ unless otherwise noted.

Parameter	Symbol	Condition		Rating			Unit
				min	typ	max	
Output rise time	t_{r1}	Measurement cct 3, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$	$C_L = 15pF$	–	1.5	3	ns
	t_{r2}		$C_L = 30pF$	–	2.5	5	ns
Output fall time	t_{f1}	Measurement cct 3, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$	$C_L = 15pF$	–	1.5	3	ns
	t_{f2}		$C_L = 30pF$	–	2.5	5	ns
Output duty cycle ^{*1}	Duty1	Measurement cct 3, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^{\circ}C$, $f = 72MHz$	$C_L = 15pF$	45	–	55	%
	Duty2		$C_L = 30pF$	45	–	55	%
Output disable delay time ^{*2}	t_{PLZ}	Measurement cct 6, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^{\circ}C$, $C_L = 15pF$		–	–	100	ns
Output enable delay time ^{*2}	t_{PZL}			–	–	100	ns

*1. The duty cycle characteristic is checked the sample chips of each production lot.

*2. Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

Current consumption and Output waveform with NPC's standard crystal



f [MHz]	R [Ω]	L [mH]	Ca [fF]	Cb [pF]
50	16.12	6.88	1.48	1.18
72	–	–	–	–
100	–	–	–	–

Note. The 72MHz and 100MHz crystal parameters are confidential.

FUNCTIONAL DESCRIPTION

Standby Function

When INHN goes LOW, the oscillator stops and the oscillator output on Q becomes high impedance.

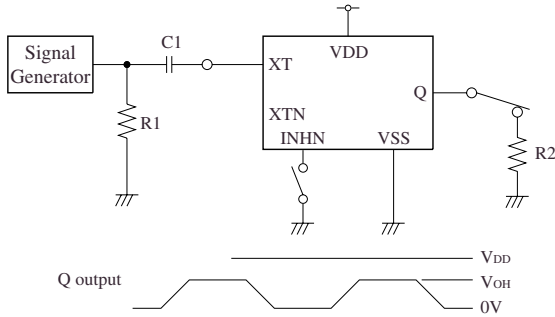
Version	INHN	Q	Oscillator
CF5026AL×	HIGH (or open)	Any f_0 , $f_0/2$, $f_0/4$, $f_0/8$, $f_0/16$ or $f_0/32$ output frequency	Normal operation
CF5026BL1, MLA		f_0	
CF5026AL×, BL1, MLA	LOW	High impedance	Stopped

Power-saving Pull-up Resistor

The INHN pull-up resistance changes in response to the input level (HIGH or LOW). When INHN goes LOW (standby state), the pull-up resistance becomes large to reduce the current consumption during standby.

MEASUREMENT CIRCUITS

Measurement cct 1



2Vp-p, 10MHz sine wave input signal

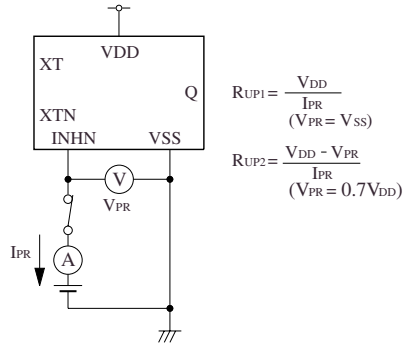
C1: 0.001μF

R1: 50Ω

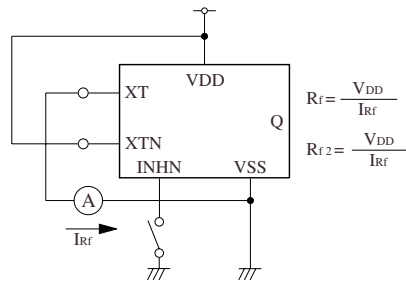
R2: 5026AL× : 412Ω (2.5V operation)
575Ω (3.0V operation)

5026BL1, MLA : 206Ω (2.5V operation)
287Ω (3.0V operation)

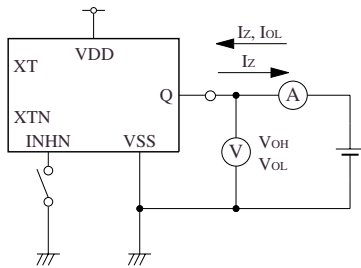
Measurement cct 4



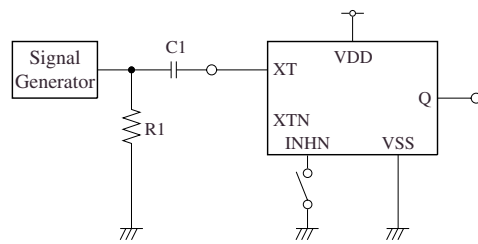
Measurement cct 5



Measurement cct 2



Measurement cct 6

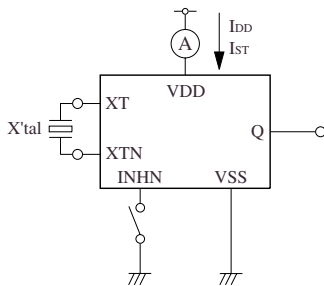


2Vp-p, 10MHz sine wave input signal

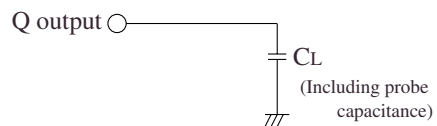
C1: 0.001μF

R1: 50Ω

Measurement cct 3

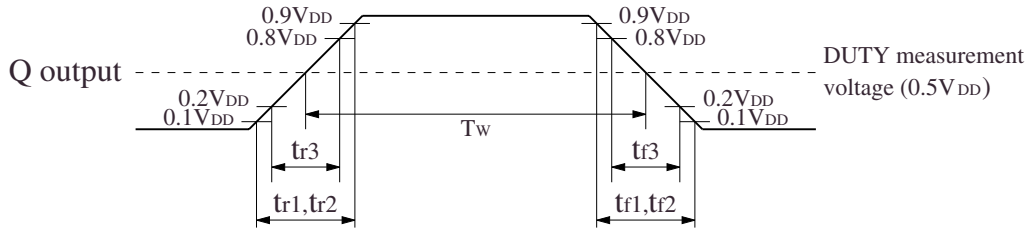


Load cct 1

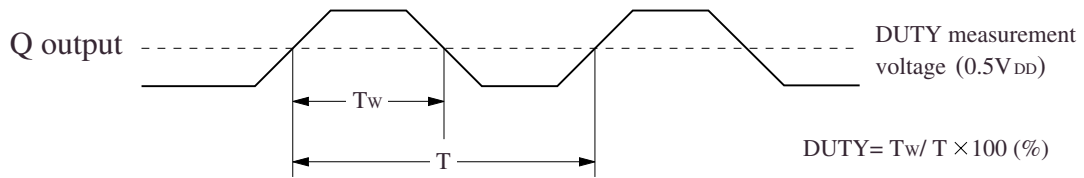


Switching Time Measurement Waveform

Output duty level, t_r , t_f

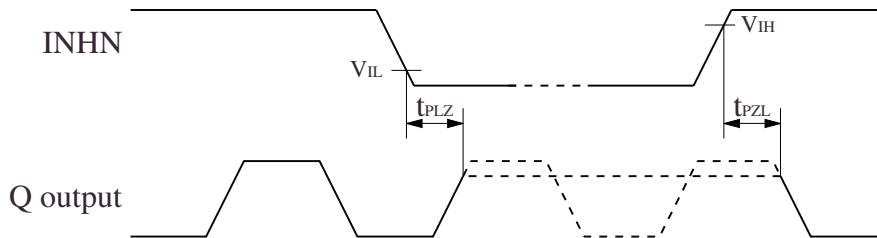


Output duty cycle



Output Enable/Disable Delay

when the device is in standby, the oscillator stops. When standby is released, the oscillator starts and stable oscillator output occurs after a short delay.



INHN input waveform $t_r = t_f \leq 10\text{ns}$

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The logo for SEIKO NPC CORPORATION, consisting of the letters 'NPC' in a bold, black, sans-serif font.

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